

HORIBA now provides a Photoluminor-D which can quantify the impurity contents in mono crystalline silicon. It is widely used for the research and development and quality control at product line.

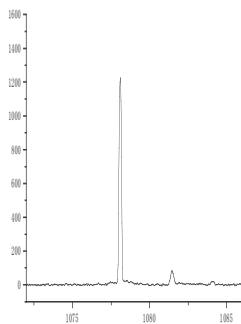
● Applications

Silicon crystals: The silicon crystal is widely used semiconductor. The photoluminescence from silicon has been studied for a long time in order to apply for quality control. The quantification impurity analysis in silicon enables you to analyze B, P, Al and As impurities in part-per trillion (ppt) range.

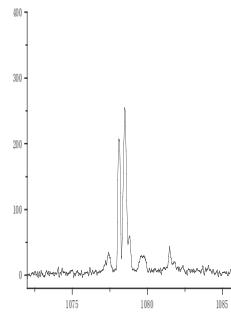
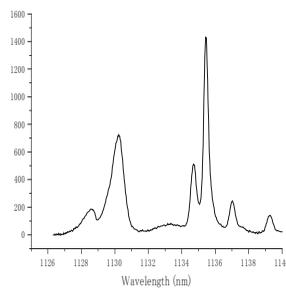
"Test Method for Photoluminescence Analysis of Single Crystal Silicon for III-V Impurities" is now approved as SEMI MF 1389-704.

● Purpose

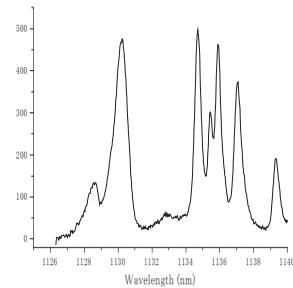
Photoluminor-D identifies and quantifies the dopant impurities from mono crystalline silicon by photoluminescence analysis.



Photoluminescence spectrum P and B doped



Photoluminescence spectrum P, B and Al doped



● Features

High Throughput

60 seconds/sample in a standard mode. High sensitivity detector and high performance monochromator make high throughput measurement possible.

Easy positioning

The TV camera is used for sample positioning. Sample positioning can be done easily and safely.

High extendibility

Additional detector, additional sample chamber can be attached. It is possible to meet all needs,

● Dopant and sensitivity

Photoluminescence measurement detects boron, phosphorus, arsenic, and aluminum as impurities in electronic grade mono crystalline silicon.

This method can be used for samples that have dopant densities between 1×10^{11} atoms/cm³ and approximately 5×10^{15} atoms/cm³.

● Software

The Amami software was developed for quantitative analysis of impurity in silicon. You can analyze by an easy operation.

● Compound semiconductors

Photoluminescence method is quite useful to evaluate composition and quality of compound semiconductors. For the instance, the PL measurement of epitaxial layers for LED's wafer and laser diodes have been routinely used. PL maps are versatile for quality control. The gas flow by the MOCVD method often gives the epitaxial wafers inhomogeneity of composition. In this case peak-shift PL maps can evaluate the distribution of composition.

We continue improving and developing more for the leading technology.

On your request, we could supply also other kinds of PL for your many purpose.

For examples:

For the mapping measurement by adding the microscope and XY stage at the entrance and CCD at the exit.

For the super high resolution measurement by adding CCD.

For the exclusive use of the compound semiconductor.

● Other application

GaN/AlGaIn multi quantum well structure GaN, InGaIn

Cryostat

We offer the glass and a metal cryostat. Maximum 36 samples can be installed. The sample is cooled with liquid helium.

Detector

Symphony IGA

Symphony IGA is the ideal choice for demanding, low light level measurements in the near infrared spectral region. With a 1024x1 pixel format and small pixel size provides exceptionally high resolution.

Highest sensitivity in NIR range

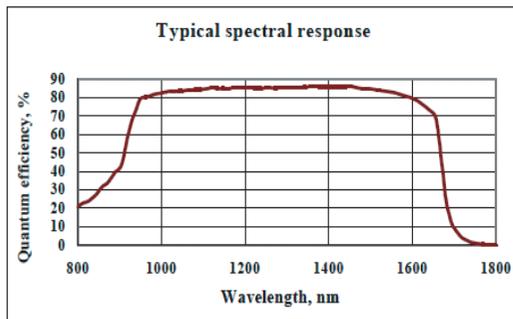
Ultra low noise (LN2 cooling)

Array detector 25micron/pixel

500micron pixel height

1024 pixel

Wavelength Range 800nm to 1600nm



Typical spectral response for IGA-1024 x 1 detector (25 °C)



Monochromator

FHR1000 Spectrometer

The Ultimate performance Spectrometer

FHR1000 spectrometer offer a unique combination of drive speed, precision and high resolution. The direct grating drive features a grating speed of greater than 300nm/second, offering users significantly reduce experiment times.

High Speed (300nm/Sec) , High accuracy, High repeatability

Focal length: 1000mm

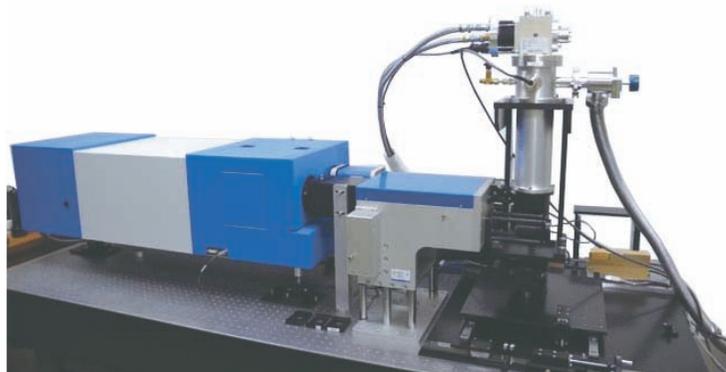
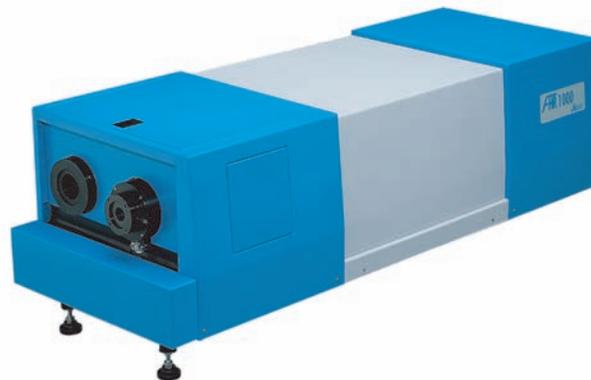
Aperture: f/9.0

Scanning Range: 0~1500nm

Grating: 110x110mm

Wavelength Accuracy: $\pm 0.03\text{nm}$

Wavelength Repeatability: $\pm 0.015\text{nm}$



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